IEUVI Resist TWG meeting

Sunday February 23rd 2020, 8:30AM-12:30PM
San Jose McEnery Convention Center, room 210D

8:00-8:30 registration

8:30 Introduction - Paolo Gargini

Speaker	Title
Christopher Arumainayagam (Wellesley College)	The role of low energy (<20 ev) electrons in EUV lithography
Seiichi Tagawa (U. Osaka)	Future prospects of photosensitized chemically amplified resist (PSCAR)
Jonathan Ma (CXRO, LBNL)	Modelling electron driven EUV processes with quantum chemistry methods
Dario Goldfarb (IBM)	IBM Research Update

10:00-10:30 coffee break

Speaker	Title
Takeo Watanabe (U. Hyogo)	EUV Resist Research Activities at NewSUBARU
Satoshi Enomoto (Toyo Gosei)	Verification studies of line width roughness reduction by using multiple chemical reactions
Robert Brainard (SUNY Polytechnic)	EUV Photoresists: What Needs to be Done
Luke Long (CXRO, LBNL)	Measurement of latent image in resist using scanning probe techniques
Greg Denbeaux (SUNY Polytechnic)	Stochastic effects in EUV resists

12:30 finish